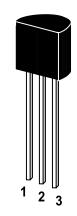
## **NPN Silicon Epitaxial Planar Transistor**

## TV VHF TUNER RF AMPLIFIER (FORWARD AGC)

The transistor is subdivided into three group,  $R \cdot O$  and Y, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package Weight approx. 0.19g

## Absolute Maximum Ratings ( $T_a = 25^{\circ}C$ )

	Symbol	Value	Unit
Collector Base Voltage	V <sub>CBO</sub>	30	V
Collector Emitter Voltage	V <sub>CEO</sub>	30	V
Emitter Base Voltage	V <sub>EBO</sub>	4	V
Collector Current	I <sub>C</sub>	20	mA
Collector Dissipation	P <sub>tot</sub>	250	mW
Junction Temperature	Tj	T <sub>j</sub> 150	
Storage Temperature Range	Τs	-55 to +150	°C







## Characteristics at $T_{amb}$ =25°C

		Symbol	Min.	Тур.	Max.	Unit
DC Current Gain						
at $V_{CE}$ =10V, $I_{C}$ =2mA	R	h <sub>FE</sub>	40	-	80	
	0	h <sub>FE</sub>	60	-	140	-
	Υ	h <sub>FE</sub>	90	-	180	
Collector Base Breakdown Voltage						
at I <sub>C</sub> =10µA		V <sub>(BR)CBO</sub>	30	-	-	V
Collector Emitter Breakdown Voltage						
at I <sub>c</sub> =5mA		$V_{(BR)CEO}$	30	-	-	V
Emitter Base Breakdown Voltage						
at I <sub>E</sub> =10µA		$V_{(BR)EBO}$	4	-	-	V
Collector Cutoff Current						
at V <sub>CB</sub> =20V		I <sub>CBO</sub>	-	-	0.1	μA
AGC Current						
I <sub>E</sub> at G <sub>pe</sub> =-30dB, f=200MHz		I <sub>AGC</sub>	-	-10	-12	mA
Reverse Transfer Capacitance						
at V <sub>CB</sub> =10V, f=1MHz		C <sub>re</sub>	-	0.35	0.5	pF
Current Gain Bandwidth Product						
at V <sub>CE</sub> =10V, I <sub>C</sub> =3mA		f⊤	400	700	-	MHz
Power Gain						
at V <sub>CE</sub> =10V, f=200MHz, R <sub>S</sub> =50 $\Omega$ , I <sub>E</sub> =-3mA		$G_{pe}$	20	24	-	dB
Noise Figure						
at V <sub>CE</sub> =10V, I <sub>E</sub> =-3mA						
f=200MHz, R <sub>s</sub> =50Ω		NF	-	2.0	3.0	dB







Dated : 16/06/2004